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Renesas Technology Corp. Customer Support Dept. April 1, 2003



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Octal Buffers/Line Drivers With 3 State Outputs



ADE-205-007A (Z) 2nd. Edition Mar. 1993

Description

The HD74BC244A provides high drivability and operation equal to or better than high speed bipolar standard logic IC by using Bi-CMOS process. The device features low power dissipation that is about 1/5 of high speed bipolar logic IC, when the frequency is 10 MHz. The device has eight inverter drivers with three state outputs in a 20 pin package. This device is a non inverting buffer and has two active low enables ($1\overline{G}$ and $2\overline{G}$). Each enable independently controls 4 buffers.

Features

- Input/Output are at high impedance state when power supply is off.
- Built in input pull up circuit can make input pins be open, when not used.
- TTL level input
- Wide operating temperature range $Ta = -40 \text{ to} + 85^{\circ}\text{C}$

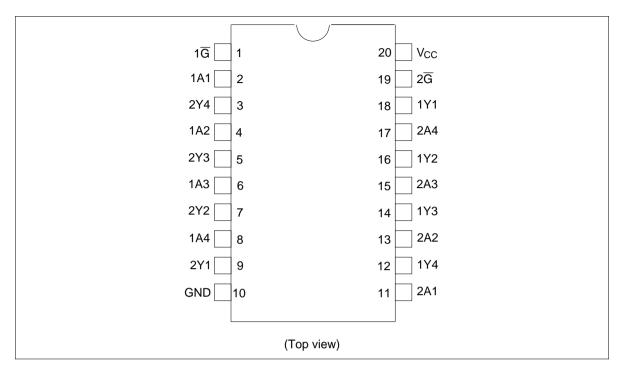
Function Table

Inputs

G	A	Output Y
Н	X	Z
L	Н	Н
L	L	L

H: High levelL: Low levelX: ImmaterialZ: High impedance

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Rating	Unit	
Supply voltage	V _{cc}	-0.5 to +7.0	V	
Input diode current	I _{IK}	±30	mA	
Input voltage	V _{IN}	-0.5 to +7.5	V	
Output voltage	V _{OUT}	-0.5 to +7.5	V	
Off state output voltage	$V_{OUT(off)}$	-0.5 to +5.5	V	
Storage temperature	Tstg	-65 to +150	°C	

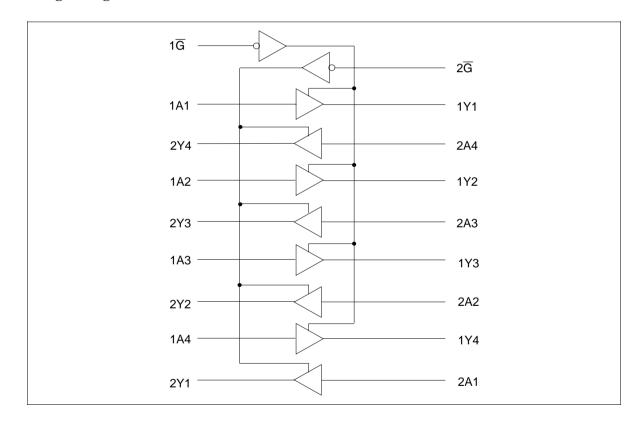
Note: 1. The absolute maximum ratings are values which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

Recommended Operating Conditions

Item	Symbol	Min	Тур	Max	Unit	
Supply voltage	V _{cc}	4.5	5.0	5.5	V	
Input voltage	V _{IN}	0	_	V _{cc}	V	
Output voltage	V _{out}	0	_	V _{cc}	V	
Operating temperature	Topr	-40	_	85	°C	
Input rise/fall time*1	t _r , t _f	0	_	8	ns/V	

Note: 1. This item guarantees maximum limit when one input switches. Waveform: Refer to test circuit of switching characteristics.

Logic Diagram



Electrical Characteristics (Ta = -40°C to +85°C)

Item	Symbol	$V_{cc}(V)$	Min	Max	Unit	Test Conditions
Input voltage	V _{IH}		2.0	_	V	
	V _{IL}		_	0.8	V	
Output voltage	V _{OH}	4.5	2.4	_	V	$I_{OH} = -3 \text{ mA}$
		4.5	2.0	_	V	$I_{OH} = -15 \text{ mA}$
	V _{OL}	4.5	_	0.5	V	I _{OL} = 48 mA
		4.5	_	0.55	V	I _{OL} = 64 mA
Input diode voltage	V _{IK}	4.5	_	-1.2	V	$I_{IN} = -18 \text{ mA}$
Input current	I ₁	5.5	_	-250	μΑ	V _{IN} = 0 V
		5.5	_	1.0	μΑ	V _{IN} = 5.5 V
		5.5	_	100	μΑ	V _{IN} = 7.0 V
Short circuit output current*1	I _{os}	5.5	-100	-225	mA	V _{IN} = 0 or 5.5 V
Off state output current	I _{OZH}	5.5	_	50	μΑ	V ₀ = 2.7 V
	I _{OZL}	5.5	_	-50	μΑ	V ₀ = 0.5 V
Supply current	I _{CCL}	5.5	_	29.5	mA	$V_{IN} = 0$ or 5.5 V All outputs is "L"
	I _{CCH}	5.5	_	0.5	mA	$V_{IN} = 0$ or 5.5 V All outputs is "H"
	I _{ccz}	5.5	_	2.5	mA	$V_{IN} = 0$ or 5.5 V All outputs is "Z"
	I _{CCT} *2	5.5	_	1.5	mA	$V_{IN} = 3.4 \text{ or } 0.5 \text{ V}$

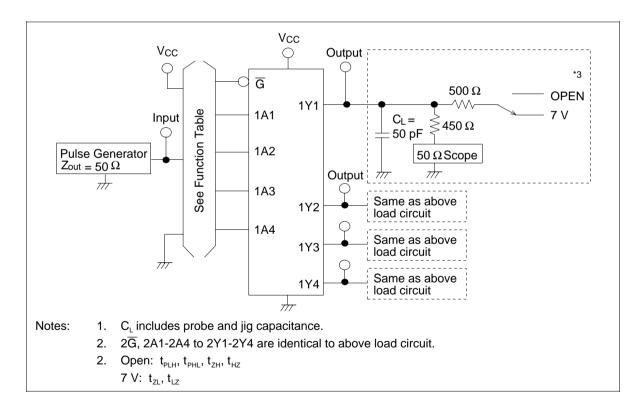
Notes: 1. Not more than one output should be shorted at a time and duration of the short circuit should not exceed one second.

^{2.} When input by the TTL level, it shows $\rm I_{\rm cc}$ increase at per one input pin.

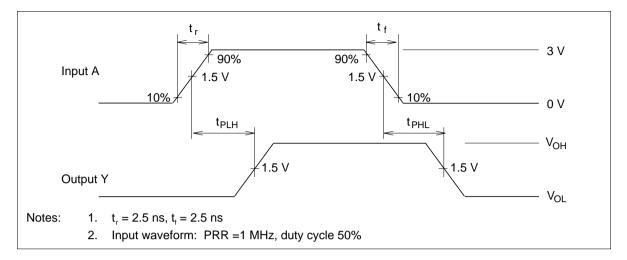
Switching Test Method $(C_L = 50 \text{ pF})$

		Ta = 25°C V _{cc} = 5.0 V		Ta = -40 to 85° C V _{cc} = 5.0 V $\pm 10\%$				
Item	Symbol	Min	Max	Min	Max	Unit	Test Conditions	
Propagation delay time	t _{PLH}	3.0	6.0	3.0	7.0	ns	See under figure	
	t _{PHL}	3.0	6.0	3.0	7.0	_		
Output enable time	t _{zH}	3.0	8.0	3.0	10.0	ns	_	
	t _{zL}	3.0	8.0	3.0	10.0	_		
Output disable time	t _{HZ}	3.0	7.0	3.0	9.0	ns	_	
	t _{LZ}	3.0	7.0	3.0	9.0	_		
Input capacitanse	C _{IN}	3.0(Typ)		_		рF	$V_{IN} = V_{CC}$ or GND	
Output capacitance	Co	15.0(T	yp)	_		pF	$V_{o} = V_{cc}$ or GND	

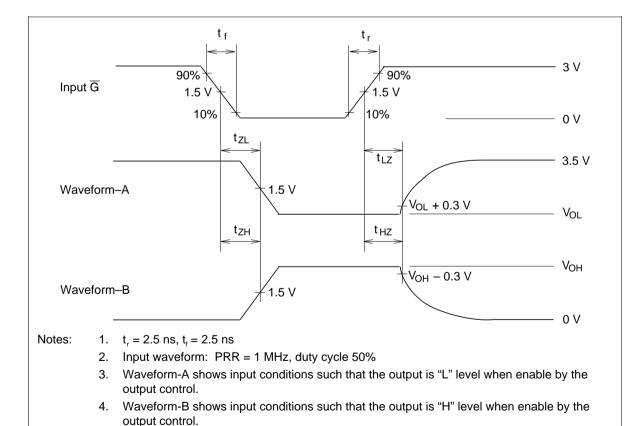
Test Circuit



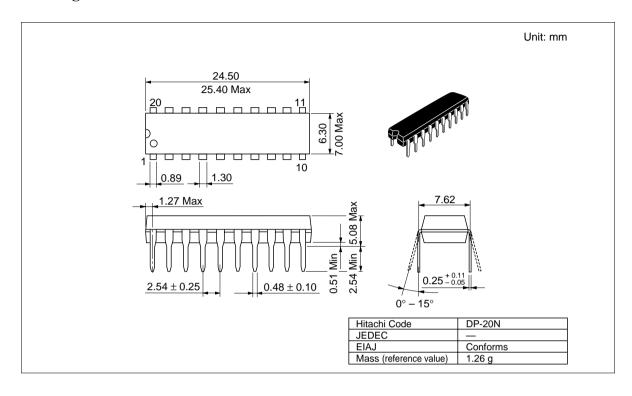
Waveforms-1

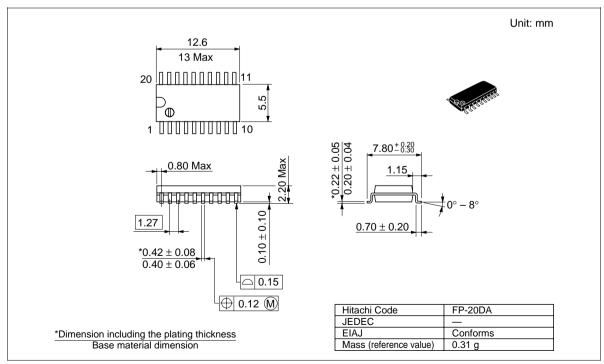


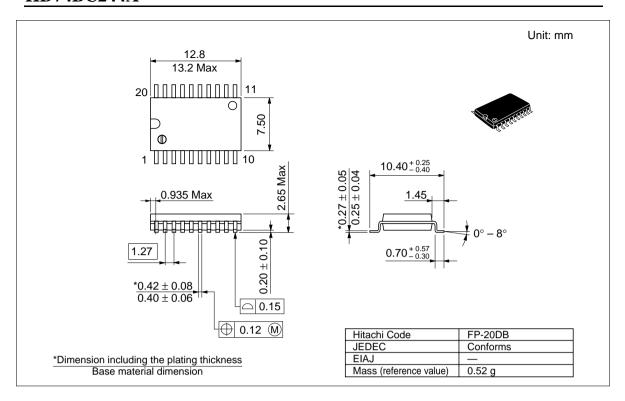
Waveforms-2

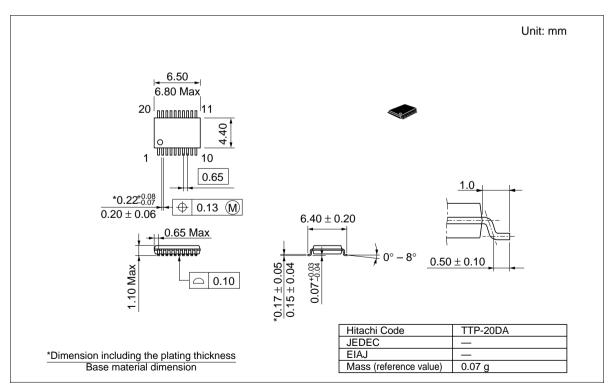


Package Dimensions









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